

SFF50N20N
SFF50N20P

14849 Firestone Boulevard · La Mirada, CA 90638
 Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424

Designer's Data Sheet

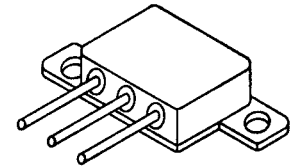
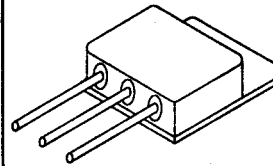
FEATURES:

- Rugged construction with polysilicon gate
- Low RDS(on) and high transconductance
- Excellent high temperature stability
- Very fast switching speed
- Fast recovery and superior dv/dt performance
- Increased reverse energy capability
- Low input and transfer capacitance for easy paralleling
- Ceramic Seals for improved hermeticity
- Hermetically sealed package
- TX, TXV and Space Level screening available
- Replaces: IXTH50N20 Types

50 AMP
200 VOLTS
0.055 Ω
N-CHANNEL
POWER MOSFET

TO-258 (N)

TO-259 (P)

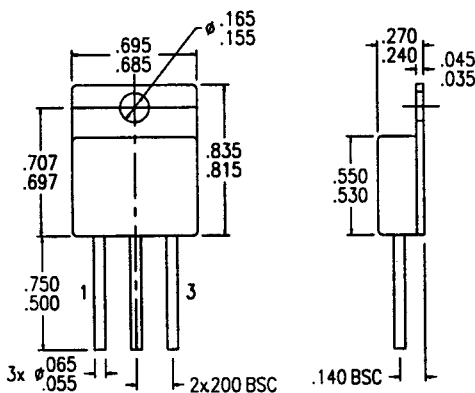


MAXIMUM RATINGS:

CHARACTERISTIC	SYMBOL	VALUE	UNIT
Drain to Source Voltage	V _{DS}	200	Volts
Gate to Source Voltage	V _{GS}	±20	Volts
Continuous Drain Current	I _D	50	Amps
Operating and Storage Temperature	T _{op} & T _{stg}	-55 to +150	°C
Thermal Resistance, Junction to Case	R _{θJC}	0.83	°C/W
Total Device Dissipation @ TC=25°C	P _D	150	Watts
Total Device Dissipation @ TC=55°C		114	

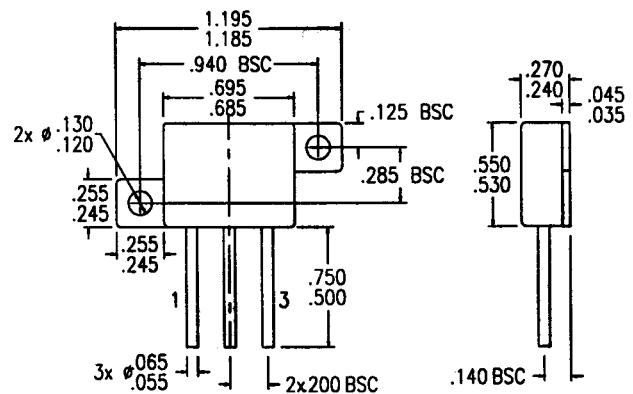
PACKAGE OUTLINE: TO-258 (N)

PIN OUT:
PIN 1: DRAIN
PIN 2: SOURCE
PIN 3: GATE



PACKAGE OUTLINE: TO-259 (P)

PIN OUT:
PIN 1: DRAIN
PIN 2: SOURCE
PIN 3: GATE



NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: F00133 B

MED

SFF50N20N SFF50N20P

PRELIMINARY



SOLID STATE DEVICES, INC

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ELECTRICAL CHARACTERISTICS @ T_J=25° C (Unless Otherwise Specified)

RATING	SYMBOL	MIN	TYP	MAX	UNIT	
Drain to Source Breakdown Voltage (V _{GS} =0 V, I _D =250μA)	BV _{DSS}	200	---	---	V	
Drain to Source on State Resistance (V _{GS} =10 V, I _D =60% Rated ID)	R _{DS(on)}	---	---	0.055	Ω	
On State Drain Current (V _{DS} >I _{D(on)} X R _{DS(on)} Max, V _{GS} =10 V)	I _{D(on)}	50	---	---	A	
Gate Threshold Voltage (V _{DS} =V _{GS} , I _D =4mA)	V _{GS(th)}	2.0	---	4.0	V	
Forward Transconductance (V _{DS} >I _{D(on)} X R _{DS(on)} Max, I _{DS} =50% rated ID)	g _{fs}	20	25	---	S(Ω)	
Zero Gate Voltage Drain Current (V _{DS} =max rated voltage, V _{GS} =0 V) (V _{DS} =80% rated V _{DS} , V _{GS} =0 V, T _A =125° C)	I _{DSS}	---	---	250 1000	μA	
Gate to Source Leakage Forward Gate to Source Leakage Reverse	I _{GSS}	At rated V _{GS} ---	---	+100 -100	nA	
Total Gate Charge Gate to Source Charge Gate to Drain Charge	Q _g Q _{gs} Q _{gd}	V _{GS} =10 Volts 50% rated V _{DS} 50% Rated ID	---	190 35 95	220 50 120	nC
Turn on Delay Time Rise Time Turn Off Delay Time Fall Time	t _{d(on)} t _r t _{d(off)} t _f	V _{DD} =50% rated V _{DS} 50% rated ID R _G =6.2Ω V _{GS} =10V	---	28 33 110 30	35 40 130 35	nsec
Diode Forward Voltage (I _S =rated ID, V _{GS} =0 V, T _J =25° C)	V _{SD}	---	---	1.5	V	
Diode Reverse Recovery Time Reverse Recovery Charge	t _{rr} Q _{RR}	T _J =25° C I _F =10 A di/dt=100 A/μsec	---	---	225 ---	nsec μC
Input Capacitance Output Capacitance Reverse Transfer Capacitance	C _{iss} C _{oss} C _{rss}	V _{GS} =0 Volts V _{DS} =25 Volts f= 1 MHz	---	4400 800 285	---	pF

SAFE OPERATING AREA (S.O.A.)
T_C = 25 C, D.C. CONDITION

